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#### April 2015

## FPF1039 Low On-Resistance, Slew-Rate-Controlled Load Switch

#### Features

- 1.2 V to 5.5 V Input Voltage Operating Range
- Typical R<sub>ON</sub>:
  - $~20~m\Omega$  at V\_{IN}=5.5 V  $\,$
  - 21 m $\Omega$  at V\_{IN}=4.5 V
  - 37 m $\Omega$  at V\_{IN}=1.8 V
  - 75 mΩ at V<sub>IN</sub>=1.2 V
- Slew Rate / Inrush Control with t<sub>R</sub>: 2.7 ms (Typical)
- 3.5 A Maximum Continuous Current Capability
- Output Capacitor Discharge Function
- Low <1 µA Shutdown Current</p>
- ESD Protected: Above 8 kV HBM, 1.5 kV CDM
- GPIO / CMOS-Compatible Enable Circuitry

#### Applications

- HDD, Storage, and Solid-State Memory Devices
- Portable Media Devices, UMPC, Tablets, MIDs
- Wireless LAN Cards and Modules
- SLR Digital Cameras
- Portable Medical Devices
- GPS and Navigation Equipment
- Industrial Handheld and Enterprise Equipment

## Description

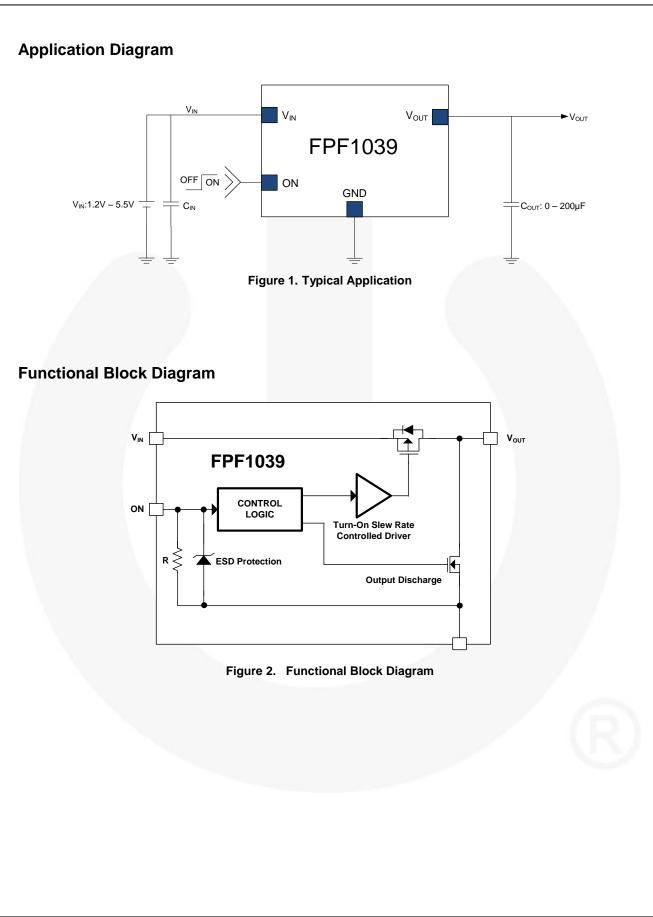
The FPF1039 advanced load-management switch target applications requiring a highly integrated solution for disconnecting loads powered from DC power rail (<6 V) with stringent shutdown current targets and high load capacitances (up to 200  $\mu$ F). The FPF1039 consists of slew-rate controlled low-impedance MOSFET switch (21 m $\Omega$  typical) and other integrated analog features. The slew-rate controlled turn-on characteristic prevents inrush current and the resulting excessive voltage droop on power rails.

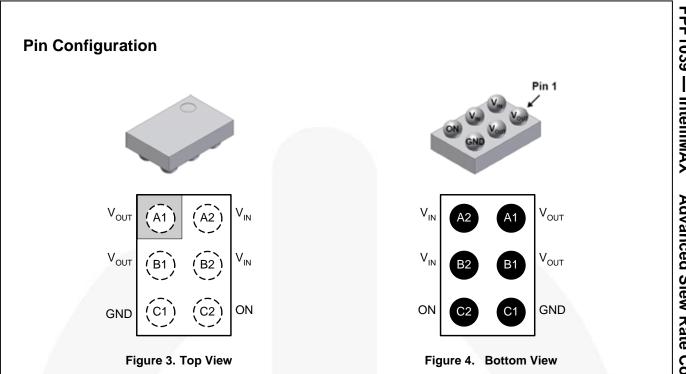
This device has exceptionally low shutdown current drain (<1  $\mu$ A maximum) that facilitates compliance in low standby power applications. The input voltage range operates from 1.2 V to 5.5 V DC to support a wide range of applications in consumer, optical, medical, storage, portable, and industrial device power management.

Switch control is managed by a logic input (active HIGH) capable of interfacing directly with low-voltage control signal / GPIO with no external pull-up required. The device is packaged in advanced fully "green" 1mm x1.5 mm Wafer-Level Chip-Scale Packaging (WLCSP); providing excellent thermal conductivity, small footprint, and low electrical resistance for wider application usage.

Part Number	Top Mark	Switch R <sub>oN</sub> (Typical) at 4.5 V <sub>IN</sub>	Input Buffer	Output Discharge	ON Pin Activity	t <sub>R</sub>	Package
FPF1039UCX	QF	21 mΩ	CMOS	65Ω	Active HIGH	2.7 ms	6-Bump, WLCSP, 1.0 mm x 1.5 mm, 0.5 mm Pitch
FPF1039BUCX	QF	21 mΩ	CMOS	65Ω	Active HIGH	2.7 ms	6-Bump, WLCSP with Backside Laminate, 1.0 mm x 1.5 mm, 0.5 mm Pitch

#### **Ordering Information**





## **Pin Definitions**

Pin #	Name	Description
A1, B1	Vout	Switch Output
A2, B2	V <sub>IN</sub>	Supply Input: Input to the Power Switch
C1	GND	Ground
C2	ON	ON/OFF Control, Active High - GPIO Compatible

## Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Par	Min.	Max.	Unit		
V <sub>IN</sub>	$V_{\text{IN}}$ , $V_{\text{OUT}}$ , $V_{\text{ON}}$ to GND		-0.3	6.0	V	
I <sub>SW</sub>	Maximum Continuous Switch Curren	t		3.5	А	
PD	Power Dissipation at $T_A=25^{\circ}C$			1.2	W	
T <sub>STG</sub>	Storage Junction Temperature		-65	+150	°C	
T <sub>A</sub>	Operating Temperature Range		-40	+85	°C	
	Thermal Desistance, Junction to Am	hight		85 <sup>(1)</sup>	°C/W	
$\Theta_{JA}$	Thermal Resistance, Junction-to-Ambient			110 <sup>(2)</sup>	0/00	
ESD	Electrostatic Discharge Conshility	Human Body Model, JESD22-A114	8.0		kV	
ESD	Electrostatic Discharge Capability	Charged Device Model, JESD22-C101	1.5			

Notes:

1. Measured using 2S2P JEDEC std. PCB.

2. Measured using 2S2P JEDEC PCB COLD PLATE method.

## **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameters	Min.	Max.	Unit
V <sub>IN</sub>	Input Voltage	1.2	5.5	V
TA	Ambient Operating Temperature	-40	+85	°C

FPF1039 — IntelliMAX<sup>TM</sup> Advanced Slew Rate Controlled Load Switch

## **Electrical Characteristics**

Unless otherwise noted,  $V_{IN}$ =1.2 to 5.5V and  $T_A$ =-40 to +85°C; typical values are at  $V_{IN}$ =4.5V and  $T_A$ =25°C.

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units	
Basic Oper	ration				1		
VIN	Input Voltage		1.2		5.5	V	
I <sub>Q(OFF)</sub>	Off Supply Current	V <sub>ON</sub> =GND, V <sub>OUT</sub> =Open			1.0	μA	
I <sub>SD</sub>	Shutdown Current	V <sub>ON</sub> =GND, V <sub>OUT</sub> =GND		0.2	1.0	μA	
lq	Quiescent Current	I <sub>OUT</sub> =0 mA		5.5	8.0	μA	
		V <sub>IN</sub> =5.5 V, I <sub>OUT</sub> =1 A <sup>(3)</sup>		20	24	1	
		V <sub>IN</sub> =4.5 V, I <sub>OUT</sub> =1 A, T <sub>A</sub> =25°C 21		21	25		
P	On Resistance	V <sub>IN</sub> =3.3 V, I <sub>OUT</sub> =500 mA <sup>(3)</sup>	24 29				
R <sub>ON</sub>		V <sub>IN</sub> =2.5 V, I <sub>OUT</sub> =500 mA <sup>(3)</sup>	1	28	35	mΩ	
		V <sub>IN</sub> =1.8 V, I <sub>OUT</sub> =250 mA <sup>(3)</sup>		37	45		
		V <sub>IN</sub> =1.2 V, I <sub>OUT</sub> =250 mA, T <sub>A</sub> =25°C		75	100		
R <sub>PD</sub>	Output Discharge RPULL DOWN	$V_{IN}$ =4.5 V, $V_{ON}$ =0 V, $I_{FORCE}$ =20 mA, $T_A$ =25°C		65	85	Ω	
V <sub>IH</sub>	On Input Logic HIGH Voltage		1.0			V	
VIL	On Input Logic LOW Voltage				0.4	V	
I <sub>ON</sub>	On Input Leakage				1.5	μA	
Dynamic C	haracteristics						
t <sub>DON</sub>	Turn-On Delay <sup>(4)</sup>			1.7		ms	
t <sub>R</sub>	V <sub>OUT</sub> Rise Time <sup>(4)</sup>	V <sub>IN</sub> =4.5 V, R <sub>L</sub> =5 Ω, C <sub>L</sub> =100 μF, T <sub>A</sub> =25°C		2.7		ms	
t <sub>ON</sub>	Turn-On Time <sup>(6)</sup>			4.4		ms	
t <sub>DOFF</sub>	Turn-Off Delay <sup>(4,5)</sup>			0.5		ms	
t <sub>F</sub>	V <sub>OUT</sub> Fall Time <sup>(4,5)</sup>	V <sub>IN</sub> =4.5 V, R <sub>L</sub> =150 Ω, C <sub>L</sub> =100 μF, T <sub>A</sub> =25°C <sup>(5)</sup>		10.0		ms	
toff	Turn-Off <sup>(5,7)</sup>	-20 0		10.5		ms	

Notes:

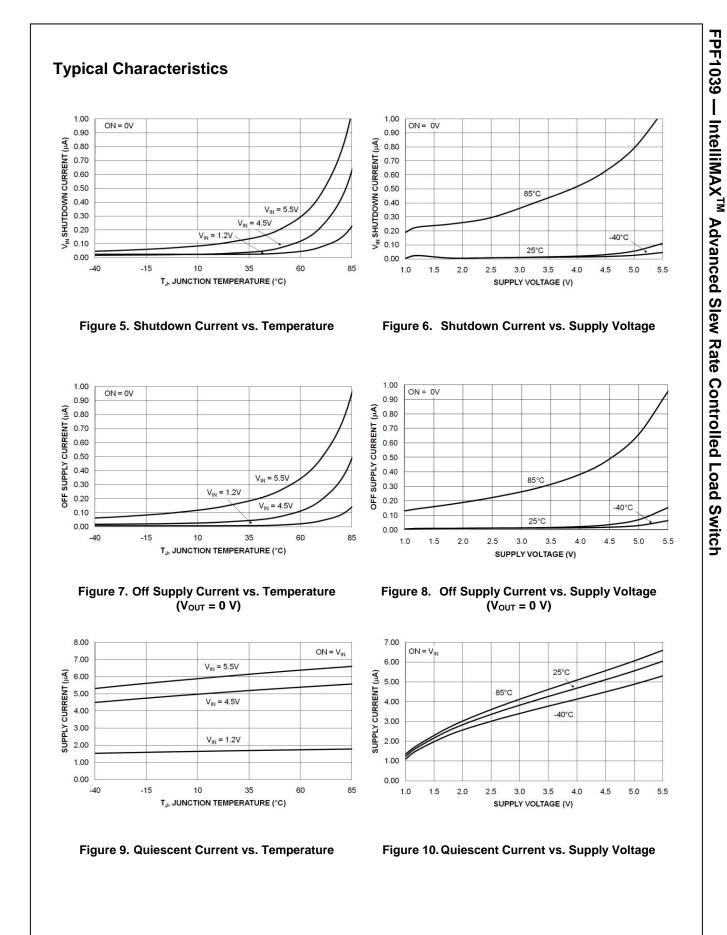
3. This parameter is guaranteed by design and characterization; not production tested.

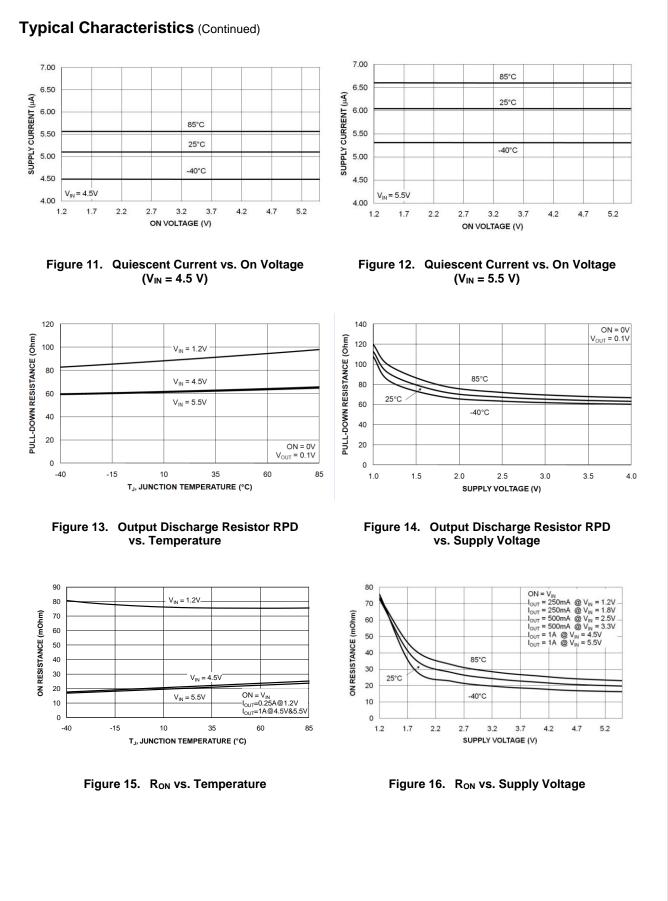
4.  $t_{DON}/t_{DOFF}/t_R/t_F$  are defined in Figure 32.

5. Output discharge enabled during off-state.

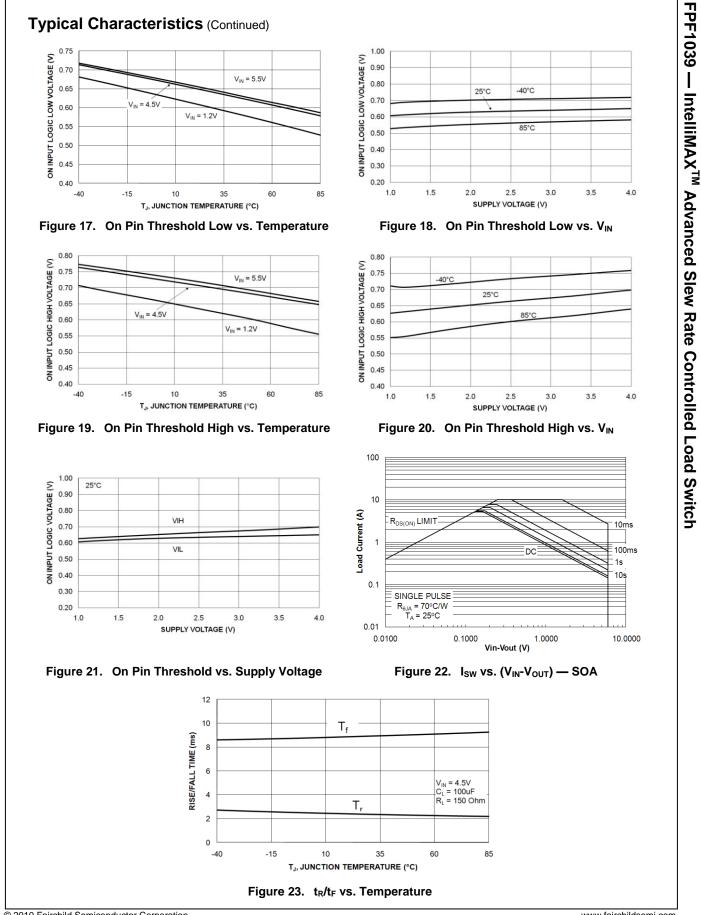
6. t<sub>ON</sub>=t<sub>R</sub> + t<sub>DON</sub>

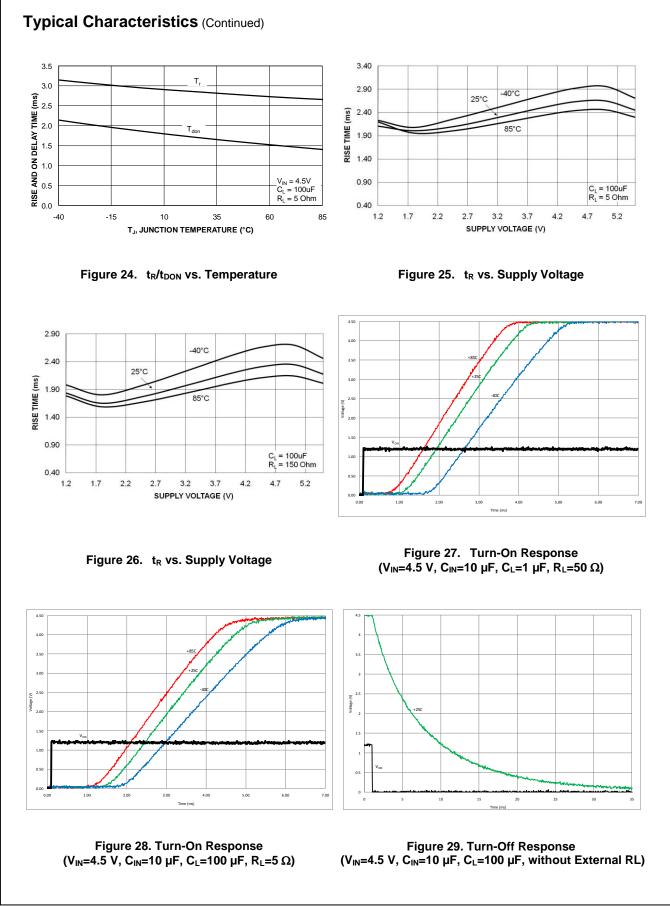
7. t<sub>OFF</sub>=t<sub>F</sub> + t<sub>DOFF</sub>

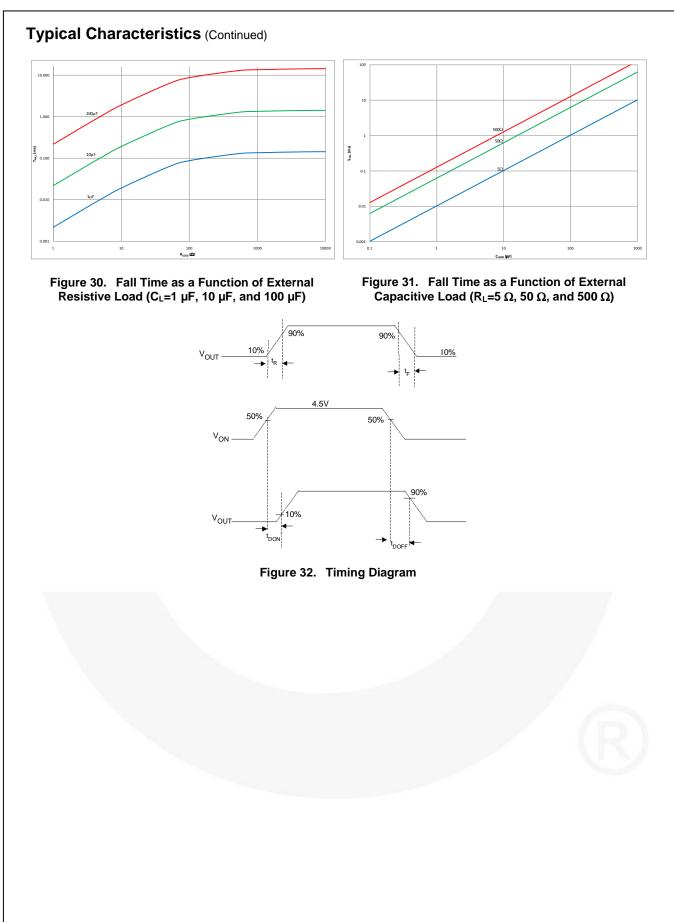




FPF1039 — IntelliMAX<sup>TM</sup> Advanced Slew Rate Controlled Load Switch







FPF1039 — IntelliMAX<sup>TM</sup> Advanced Slew Rate Controlled Load Switch

## **Application Information**

#### **Input Capacitor**

This IntelliMAX<sup>TM</sup> switch doesn't require an input capacitor. To reduce device inrush current, a 0.1  $\mu$ F ceramic capacitor, C<sub>IN</sub>, is recommended close to the VIN pin. A higher value of C<sub>IN</sub> can be used to reduce the voltage drop experienced as the switch is turned on into a large capacitive load.

#### **Output Capacitor**

While this switch works without an output capacitor: if parasitic board inductance forces  $V_{OUT}$  below GND when switching off; a 0.1  $\mu$ F capacitor,  $C_{OUT}$ , should be placed between  $V_{OUT}$  and GND.

#### Fall Time

Device output fall time can be calculated based on RC constant of the external components as follows:

$$t_{\rm F} = R_{\rm L} \times C_{\rm L} \times 2.2 \tag{1}$$

where  $t_F$  is 90% to 10% fall time,  $R_L$  is output load, and  $C_L$  is output capacitor.

The same equation works for a device with a pull-down output resistor.  $R_L$  is replaced by a parallel connected pull-down and an external output resistor combination as:

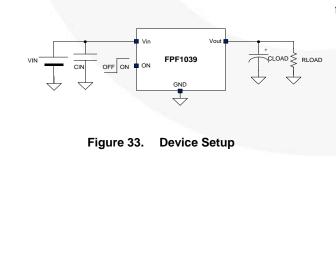
$$t_{F} = \frac{R_{L} \times R_{PD}}{R_{L} + R_{PD}} \times C_{L} \times 2.2$$
(2)

where  $t_F$  is 90% to 10% fall time,  $R_L$  is output load,  $R_{PD}$ =65  $\Omega$  is output pull-down resistor, and  $C_L$  is the output capacitor.

#### **Resistive Output Load**

If resistive output load is missing, the IntelliMAX switch without a pull-down output resistor does not discharge the output voltage. Output voltage drop depends, in that case, mainly on external device leaks.

#### **Application Specifics**



At maximum operational voltage ( $V_{IN}$ =5.5 V), device inrush current might be higher than expected. Spike current should be taken into account if  $V_{IN}$ >5 V and the output capacitor is much larger than the input capacitor. Input current can be calculated as:

$$I_{IN}(t) \approx \frac{V_{OUT}(t)}{R_{LOAD}} + (C_{LOAD} - C_{IN}) \frac{dV_{OUT}(t)}{dt}$$
(3)

where switch and wire resistances are neglected and capacitors are assumed ideal.

Estimating  $V_{OUT}(t)=V_{IN}/10$  and using experimental formula for slew rate  $(dV_{OUT}(t)/dt)$ , spike current can be written as:

$$\max(I_{\rm IN}) = \frac{V_{\rm IN}}{10R_{\rm LOAD}} + (C_{\rm LOAD} - C_{\rm IN}) \left( 0.05 V_{\rm IN} - 0.255 \right)$$
(4)

where supply voltage  $V_{\text{IN}}$  is in volts, capacitances are in micro farads, and resistance is in ohms.

Example: If  $V_{IN}$ =5.5V,  $C_{LOAD}$ =100 µF,  $C_{IN}$ =10 µF, and  $R_{LOAD}$ =50  $\Omega$ ; calculate the spike current by:

$$\max(I_{\rm IN}) = \frac{5.5}{10^{*}50} + (100 - 10)(0.05^{*}5.5 - 0.255)A = 1.8A$$
 (5)

Maximum spike current is 1.8 A, while average rampup current is:

$$I_{IN}(t) \approx \frac{V_{OUT}(t)}{R_{LOAD}} + (C_{LOAD} - C_{IN}) \frac{dV_{IN}(t)}{dt}$$

$$\approx 2.75 / 50 + 100 * 0.0022 = 0.275 \text{ A}$$
(6)

#### **Output Discharge**

FPF1039 contains a 65  $\Omega$  on-chip pull-down resistor for quick output discharge. The resistor is activated when the switch is turned off.

#### **Recommended Layout**

For best thermal performance and minimal inductance and parasitic effects, it is recommended to keep input and output traces short and capacitors as close to the device as possible. Figure 34 is a recommended layout for this device to achieve optimum performance.

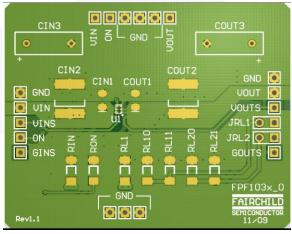
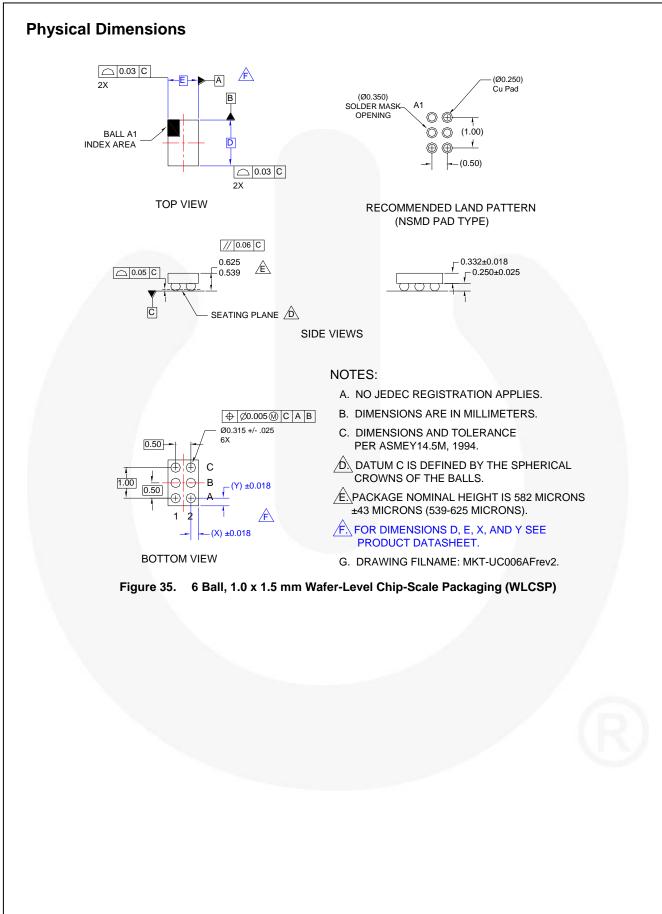


Figure 34. Recommended Land Pattern, Layout



FPF1039 — Advance Load Management Switch Management Switch Advance Load Management Switch

### **Nominal Values**

Bump	Overall Package	Silicon	Solder Bump	Solder Bump	
Pitch	Height	Thickness	Height	Diameter	
0.5 mm	0.582 mm	0.332 mm	0.250 mm		

### **Product-Specific Dimensions**

Product	D	E	Х	Y
FPF1039UCX	1.46 mm ±0.03	0.96 mm ±0.03	0.230 mm	0.230 mm
FPF1039BUCX	1.46 mm ±0.03	0.96 mm ±0.03	0.230 mm	0.230 mm



FPF1039 —

No Identification Needed

Obsolete

Full Production

Not In Production

Rev. 174

changes at any time without notice to improve the design.

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